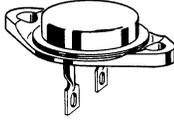


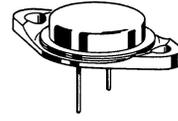
# 2N1651 thru 2N1653 (Germanium)

# 2N2285 thru 2N2287 (Germanium)



**CASE 161**  
(TO-41)

2N1651 thru 2N1653  
Collector connected to case



**CASE 3A**  
(TO-3 modified)

2N2285 thru 2N2287

PNP Germanium power transistors designed for high-current switching applications requiring low saturation voltages and fast switching times in addition to good safe operating area.

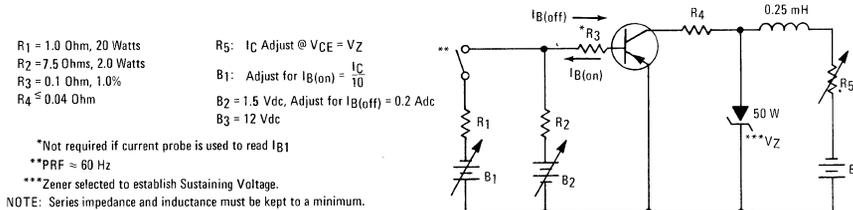
### MAXIMUM RATINGS

Rating	Symbol	2N1651 2N2285	2N1652 2N2286	2N1653 2N2287	Unit
Collector-Emmitter Voltage	$V_{CEO}$	30	60	80	Vdc
Collector-Base Voltage	$V_{CB}$	60	100	120	Vdc
Emmitter-Base Voltage	$V_{EB}$	←	1.5	→	Vdc
Collector Current - Continuous	$I_C$	←	25	→	Adc
Base Current - Continuous	$I_B$	←	5.0	→	Adc
Total Device Dissipation @ $T_C = 25^\circ C$ Derate above $25^\circ C$	$P_D$	←	106 1.25	→	Watts W/ $^\circ C$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	←	-65 to +110	→	$^\circ C$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$\theta_{JC}$	0.8	$^\circ C/W$

**FIGURE 1 – SUSTAINING VOLTAGE TEST CIRCUIT**



## 2N1651 thru 2N1653/2N2285 thru 2N2287 (continued)

ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage ( $I_C = 100\text{ mAdc}$ , $I_B = 0$ )	$BV_{CEO}$	30 60 80	- - -	Vdc
Collector-Emitter Sustaining Voltage (See Figure 1) ( $I_C = 25\text{ Adc}$ )	$V_{CE(sus)}$	40 45 50	- - -	Vdc
Collector Cutoff Current ( $V_{CB} = 2.0\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO1}$	-	200	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CB} = 40\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 80\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO2}$	- - -	5.0 5.0 5.0	mAdc
Collector Cutoff Current ( $V_{CB} = 40\text{ Vdc}$ , $I_E = 0$ , $T_C = 100^\circ\text{C}$ ) (+0, -3.0°C) ( $V_{CB} = 80\text{ Vdc}$ , $I_E = 0$ , $T_C = 100^\circ\text{C}$ ) (+0, -3.0°C) ( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ , $T_C = 100^\circ\text{C}$ ) (+0, -3.0°C)	$I_{CBO3}$	- - -	35 35 35	mAdc
Collector Cutoff Current ( $V_{CB} = 60\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 100\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 120\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO4}$	- - -	20 20 20	mAdc
Emitter Cutoff Current ( $V_{EB} = 1.5\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	-	50	mAdc

### ON CHARACTERISTICS

DC Current Gain ( $I_C = 10\text{ Adc}$ , $V_{CE} = 2.0\text{ Vdc}$ ) ( $I_C = 25\text{ Adc}$ , $V_{CE} = 1.5\text{ Vdc}$ )	$h_{FE}$	35 20	140 -	-
Collector-Emitter Saturation Voltage ( $I_C = 25\text{ Adc}$ , $I_B = 2.5\text{ Adc}$ )	$V_{CE(sat)}$	-	0.30	Vdc
Base-Emitter Saturation Voltage ( $I_C = 25\text{ Adc}$ , $I_B = 2.5\text{ Adc}$ )	$V_{BE(sat)}$	-	0.65	Vdc

### SMALL-SIGNAL CHARACTERISTICS

Small-Signal Current Gain ( $I_C = 0.5\text{ Adc}$ , $V_{CE} = 6.0\text{ Vdc}$ , $f = 30\text{ kHz}$ )	$h_{fe}$	20	-	-
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### SWITCHING CHARACTERISTICS

Rise Time	$(I_C = 25\text{ Adc}$ , $I_{B(on)} = 2.5\text{ Adc}$ , $I_{B(off)} = 2.5\text{ Adc}$ ) (See Figure 2)	$t_r$	-	12	$\mu\text{s}$
Storage Time		$t_s$	-	10	$\mu\text{s}$
Fall Time		$t_f$	-	8.0	$\mu\text{s}$

FIGURE 2 – SWITCHING TIME TEST CIRCUIT

